

Product Overview

2N7000: N-Channel Enhancement Mode Field Effect Transistor 60V, 200mA, 5 Ω

For complete documentation, see the data sheet.

These N-channel Small Signal MOSFETs are produced using ON Semiconductor's proprietary, high cell density, DMOS technology. These products have been designed to minimize on-state resistance while providing rugged, reliable, and fast switching performance. They can be used in most applications requiring up to 400 mA DC and can deliver pulsed currents up to 2 A. These products are particularly suited for low-voltage, low-current applications.

Features

- Voltage Controlled Small Signal Switch
- High Saturation Current Capability
- Rugged and Reliable
- High Density Cell Design for Low RDS(ON)

Applications

- Small Servo Motor Control
- Power MOSFET Gate Drivers
- Assorted Switching Applications

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	$V_{DS(s)}$ Min (V)	V_{GS} Max (V)	$V_{GS(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$R_{DS(on)}$ Max @ $V_{GS} = 2.5$ V (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} = 4.5$ V (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} = 10$ V (mΩ)	Q_g Typ @ $V_{GS} = 4.5$ V (nC)	Q_g Typ @ $V_{GS} = 10$ V (nC)	C_{iss} Typ (pF)	Package Type
2N7000	0.0955	Pb-free non AEC-Q and PPAP	Active	N-Channel	Single	60	20	3	0.2	0.35	-	5300	5000	-	-	60	TO-92-3
2N7000-D26Z	0.0837	Pb-free non AEC-Q and PPAP	Active	N-Channel	Single	60	20	3	0.2	0.35	-	5300	5000	-	-	60	TO-92-3 LF
2N7000-D74Z	0.0995	Pb-free non AEC-Q and PPAP	Active	N-Channel	Single	60	20	3	0.2	0.35	-	5300	5000	-	-	60	TO-92-3 LF
2N7000-D75Z	0.1068	Pb-free non AEC-Q and PPAP	Active	N-Channel	Single	60	20	3	0.2	0.35	-	5300	5000	-	-	60	TO-92-3 LF

For more information please contact your local sales support at www.onsemi.com.

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